

V _{CES}	650V
I _{C(100°C)}	30A
V _{CE(sat) (Typ.)}	1.6V
P _D	194W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

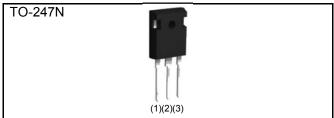
PFC

UPS

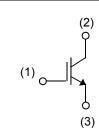
Power Conditioner

IH

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH60TS65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector - Emitter Voltage	V _{CES}	650	V	
Gate - Emitter Voltage	V _{GES}	±30	V	
Collector Current	T _C = 25°C	۱ _C	58	А
Collector Current	T _C = 100°C	Ι _C	30	А
Pulsed Collector Current	I _{CP} *1	120	А	
$T_{\rm C} = 25^{\circ}{\rm C}$		P _D	194	W
Power Dissipation	T _C = 100°C	P _D	97	W
Operating Junction Temperature	Tj	–40 to +175	°C	
Storage Temperature	T _{stg}	–55 to +175	°C	

*1 Pulse width limited by T_{imax.}

Thermal Resistance

Parameter	Symbol	Values			Unit
Faranielei	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.77	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Faranieler	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 21.0mA	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 30A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.6 2.1	2.1	V

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deveneter	Quine had	Conditions	Values				
Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1670	-		
Output Capacitance	C _{oes}	V _{GE} = 0V	-	66	-	pF	
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	27	-		
Total Gate Charge	Q_g	V _{CE} = 300V	-	58	-		
Gate - Emitter Charge	Q_{ge}	I _C = 30A	-	15	-	nC	
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	20	-		
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	27	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	40	-		
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	105	-	ns	
Fall Time	t _f	Inductive Load	-	47	-		
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	27	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	40	-		
Turn - off Delay Time t _{d(off)}		T _j = 175°C	-	120	-	ns	
Fall Time	t _f	Inductive Load	-	59	-		
		I _C = 120A, V _{CC} = 520V		-	<u>.</u>		
Reverse Bias Safe Operating Area RBSC		V _P = 650V, V _{GE} = 15V	FULL SQUARE		-		
		R _G = 60Ω, T _j = 175°C					

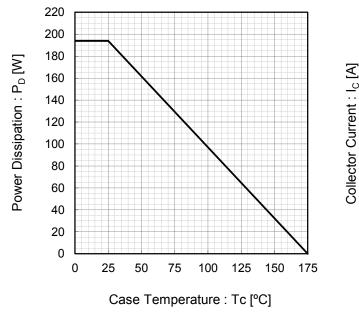


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

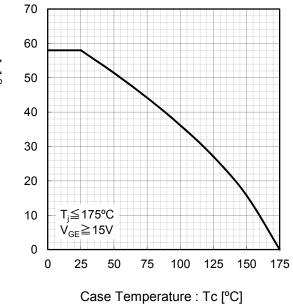
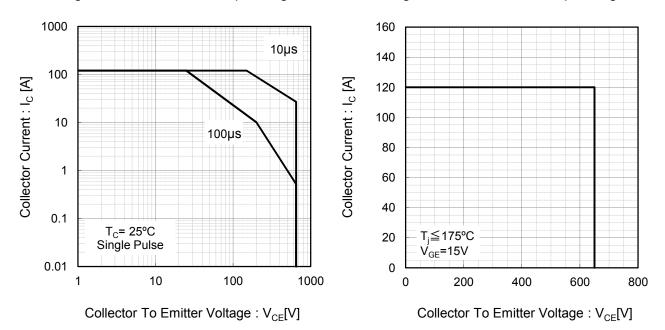


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



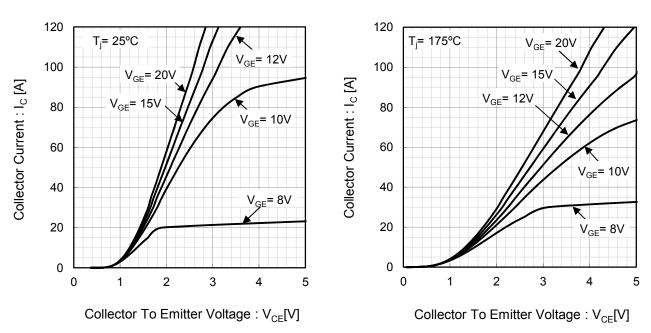
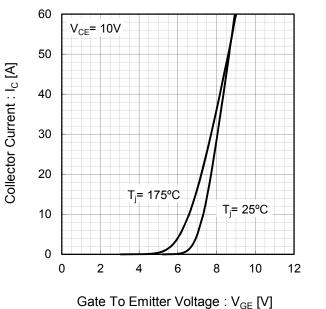


Fig.5 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics

Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

Fig.6 Typical Output Characteristics



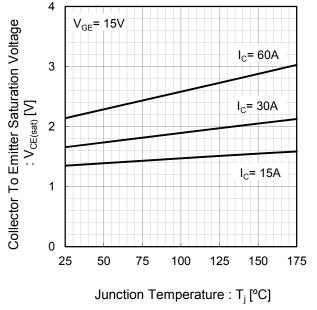


Fig.10 Typical Collector To Emitter Saturation Voltage

Electrical Characteristic Curves

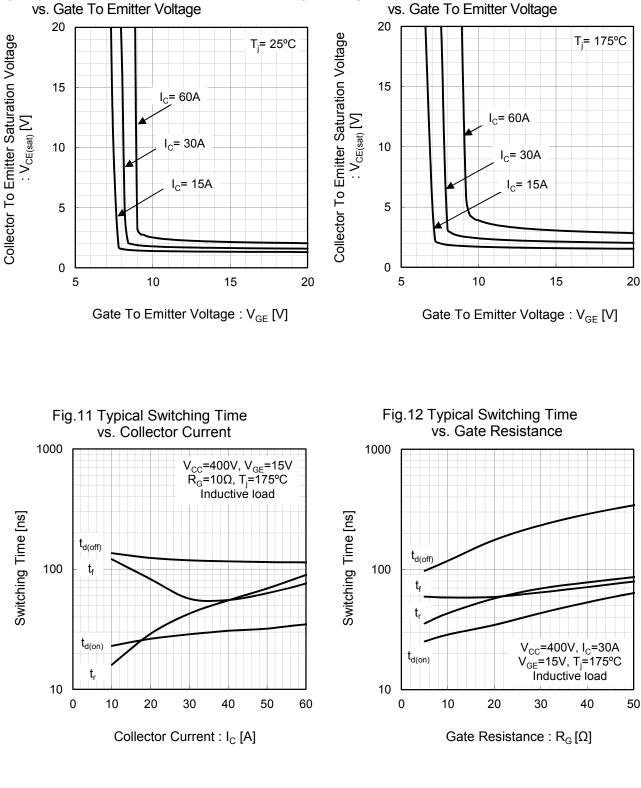
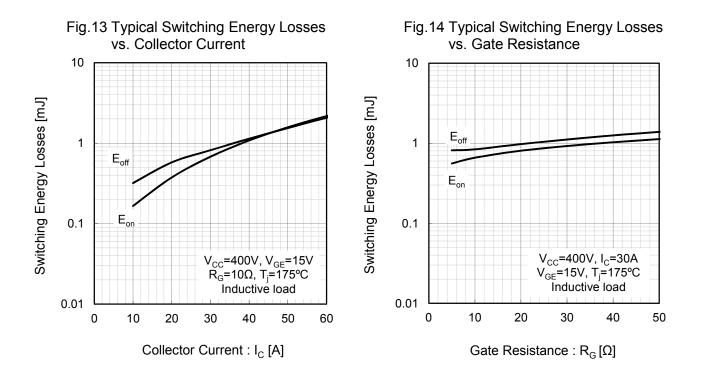


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



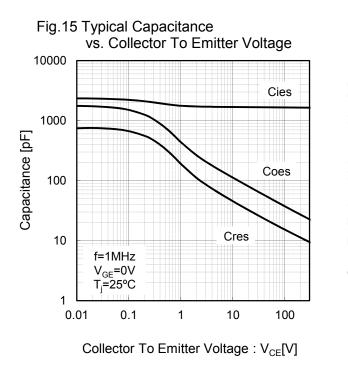
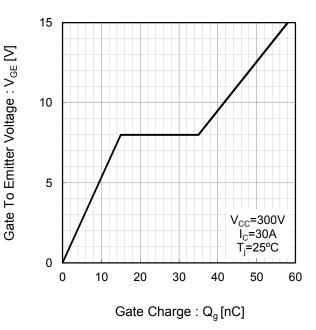


Fig.16 Typical Gate Charge



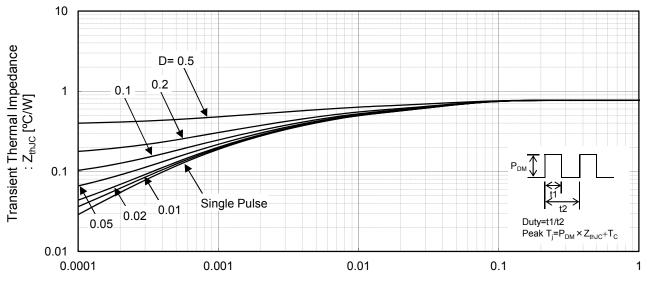


Fig.17 IGBT Transient Thermal Impedance

Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

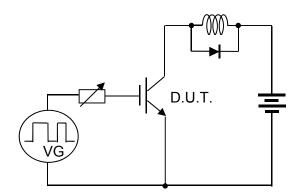
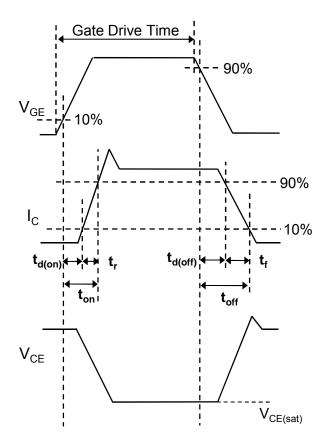


Fig.18 Inductive Load Circuit





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RGTH60TS65 - Web Page

Distribution Inventory

Part Number	RGTH60TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	450
Packing Type	Bulk
Constitution Materials List	inquiry
RoHS	Yes

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